Transistor

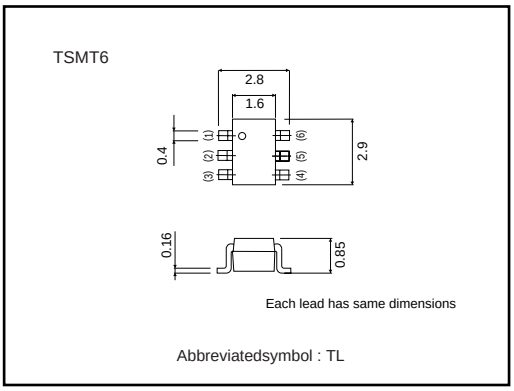
DC-DC Converter (−20V, −3.5A)

RTQ035P02

●Features

1) Low On-resistance.(80mΩ at 2.5V)
2) High Power Package.
3) High speed switching.
4) Low voltage drive.(2.5V)

●External dimensions (Units : mm)



●Applications

DC-DC converter

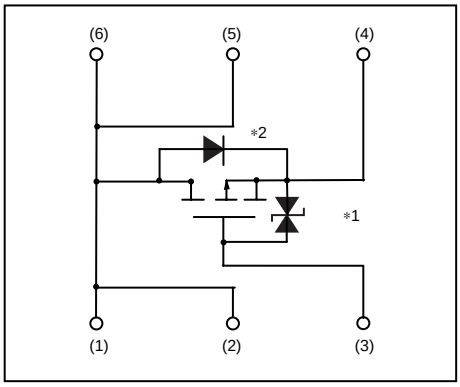
●Structure

Silicon P-channel
MOSFET

●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RTQ035P02		○

●Equivalent circuit



(1)DRAIN
(2)DRAIN
(3)GATE
(4)SOURCE
(5)DRAIN
(6)DRAIN

∗1 ESD PROTECTION DIODE
∗2 BODY DIODE

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●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain–source voltage		V_{DSS}	–20	V
Gate–source voltage		V_{GSS}	±12	V
Drain current	Continuous	I_D	±3.5	A
	Pulsed	I_{DP}	±17.5	A *1
Source current (Body diode)	Continuous	I_S	–1	A
	Pulsed	I_{SP}	–4	A *1
Total power dissipation		P_D	1.25	W*2
Channel temperature		Tch	150	°C
Range of Storage temperature		Tstg	–55~+150	°C

*1 Pw≦10μs, Duty cycle≦1%
*2 Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}=±12V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	–20	–	–	V	I_D=–1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	V_{DS}=–20V, V_{GS}=0V
Gate threshold voltage	$V_{GS(th)}$	–0.7	–	–2.0	V	V_{DS}=–10V, I_D=–1mA
Static drain-source on-state resistance	$R_{DS(on)}$*	–	50	65	mΩ	I_D=–3.5A, V_{GS}=–4.5V
		–	55	70	mΩ	I_D=–3.5A, V_{GS}=–4V
		–	80	100	mΩ	I_D=–1.75A, V_{GS}=–2.5V
Foward transfer admittance	$\lvert Y_{fs} \rvert$*	3.5	–	–	S	V_{DS}=–10V, I_D=–3.5A
Input capacitance	C_{iss}	–	1200	–	pF	V_{DS}=–10V,V_{GS}=0V f=1MHz
Output capacitance	C_{oss}	–	200	–	pF	
Reverse transfer capacitance	C_{rss}	–	130	–	pF	
Turn-on delay time	$t_{d(on)}$*	–	16	–	ns	I_D=–2A V_{DD}≒–15V V_{GS}=–4.5V R_L=7.5Ω R_{GS}=10Ω
Rise time	t_r*	–	40	–	ns	
Turn-off delay time	$t_{d(off)}$*	–	55	–	ns	
Fall time	t_f*	–	30	–	ns	
Total gate charge	Qg	–	10.5	–	nC	V_{DD}≒–15V V_{GS}=–4.5V I_D=–3.5A
Gate-source charge	Qgs	–	2.0	–	nC	
Gate-drain charge	Qgd	–	3.5	–	nC	

*PULSED

Body diode characteristics (source-drain characteristics)

Forward voltage	VSD	–	–	–1.2	V	I_S=–1A, V_{GS}=0V

●Electrical characteristic curves

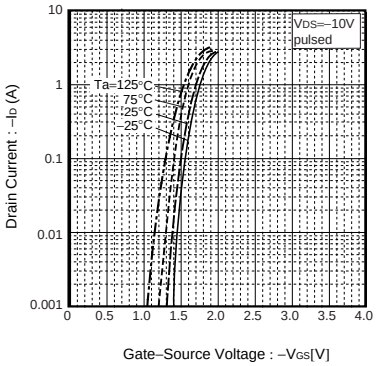

Fig.1 Typical Transfer Characteristics

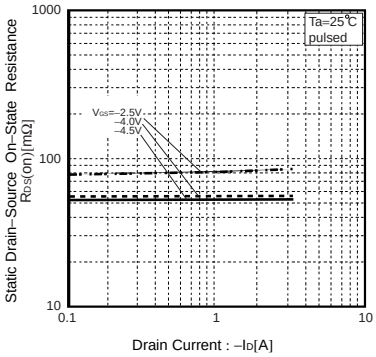

Fig.2 Static Drain−Source On−State Resistance vs.Drain Current

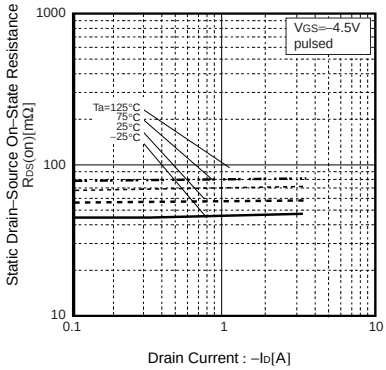

Fig.3 Static Drain−Source On−State Resistance vs.Drain Current

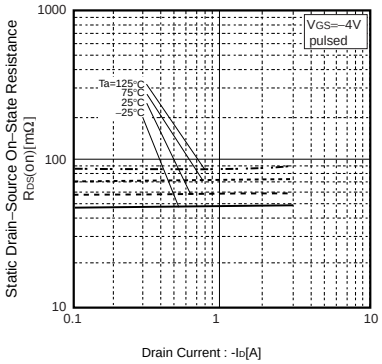

Fig.4 Static Drain−Source On−State Resistance vs.Drain−Current

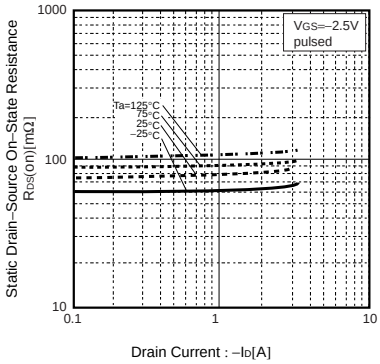

Fig.5 Static Drain−Source On−State Resistance vs.Drain−Current

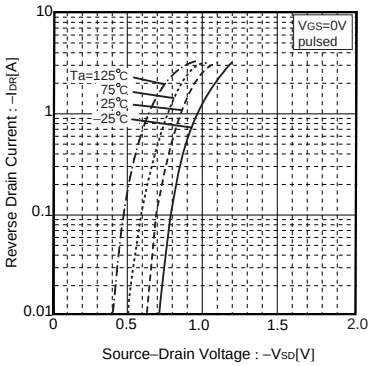

Fig.6 Reverse Drain Current vs. Source-Drain Voltage

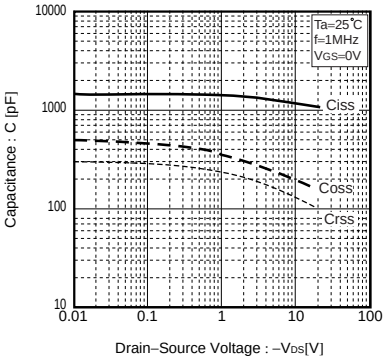

Fig.7 Typical Capactitance vs.Drain−Source Voltage

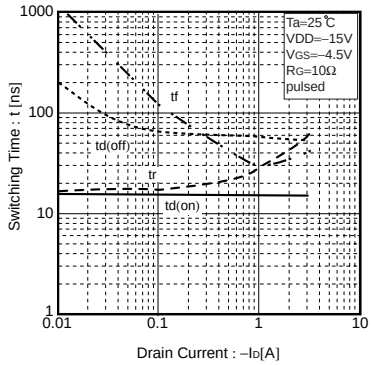

Fig.8 Switching Characteristics

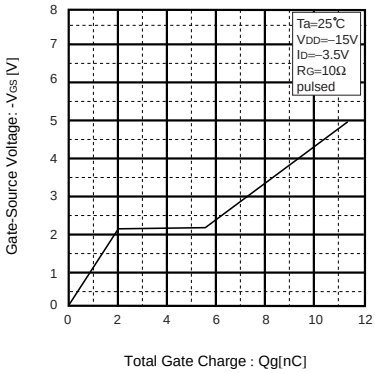

Fig.9 Dynamic Input Characteristics

●Measurement circuits

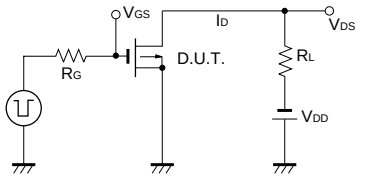

Fig.10 Switching Time Measurement Circuit

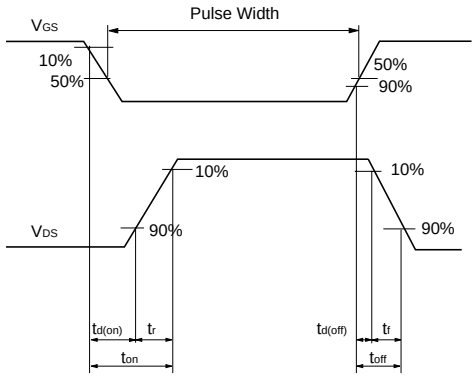

Fig.11 Switching Waveforms

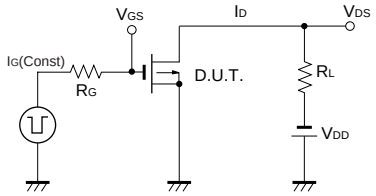

Fig.12 Gate Charge Measurement Circuit

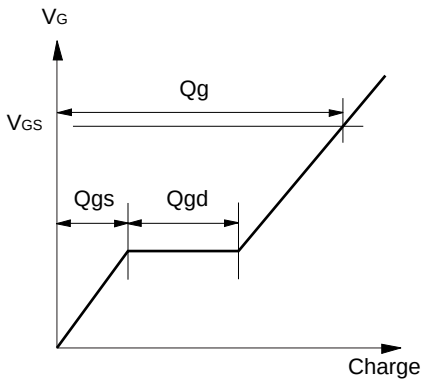

Fig.13 Gate Charge Waveforms

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